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Docket No. 740819-651

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of) Confirmation No. 7295
Shinichi IMAI) Group Art Unit: 2811
Serial No. 09/960,575) Examiner: Thomas J. Magee
Filed: September 24, 2001)
For: SEMICONDUCTOR DEVICE AND)
METHOD FOR PRODUCING THE)
SAME)

CERTIFICATE OF TRANSMISSION

I hereby certify that this correspondence is being facsimile transmitted to the United States Patent and Trademark Office: Fax No. (703) 872-9318 on January 31, 2003.

K.M. McMaous
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AMENDMENT

Commissioner for Patents

Washington, D.C. 20231

Sir:

In response to the Office Action of October 31, 2002, please amend the subject application and consider Applicants' remarks as follows:

In the Specification:

Please amend Page 6, second paragraph as follows:

A1 A semiconductor device of the present invention includes a semiconductor substrate including an active region and an isolating region provided so as to enclose the active region; a capacitance insulating film that is provided on the active region and in contact with the isolating region; an upper electrode provided on the capacitance insulating film so as to be spaced away from the isolating region; an electrode pad provided on the isolating region; a lead conductive film provided over a part of the capacitance insulating film and a part of the isolating region for connecting the upper electrode and the electrode pad; and an interlayer insulating film provided over the substrate, wherein contact holes penetrating the interlayer insulating film to reach the electrode pad are formed, and the ratio of the total sum of the exposed areas of the electrode pad

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